


## Resonant Mode Combi IGBT®

The Thunderbolt IGBT® used in this Resonant Mode Combi is a new generation of high voltage power IGBTs. Using Non- Punch Through Technology, the Thunderbolt IGBT® offers superior ruggedness and ultrafast switching speed.

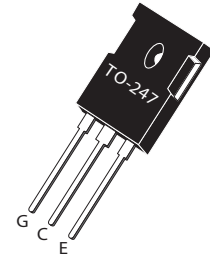
### Features

- Low Conduction Loss
- Low Gate Charge
- Ultrafast Tail Current shutoff
- Low forward Diode Voltage ( $V_f$ )
- Ultrasoft Recovery Diode

- SSOA Rated
- RoHS Compliant 

### Typical Applications

- Induction Heating
- Welding
- Medical
- High Power Telecom
- Resonant Mode Phase Shifted Bridge




### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT50GT60BRDL(G)	UNIT
$V_{CES}$	Collector-Emitter Voltage	600	Volts
$V_{GE}$	Gate-Emitter Voltage	$\pm 30$	
$I_{C1}$	Continuous Collector Current <sup>7</sup> @ $T_C = 25^\circ\text{C}$	110	Amps
$I_{C2}$	Continuous Collector Current @ $T_C = 110^\circ\text{C}$	52	
$I_{CM}$	Pulsed Collector Current <sup>1</sup> @ $T_C = 150^\circ\text{C}$	150	
SSOA	Switching Safe Operating Area @ $T_j = 150^\circ\text{C}$	150A @ 600V	
$P_D$	Total Power Dissipation	446	Watts
$T_j, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_L$	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ( $V_{GE} = 0V, I_C = 2mA$ )	600			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ( $V_{CE} = V_{GE}, I_C = 1mA, T_j = 25^\circ\text{C}$ )	3	4	5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 50A, T_j = 25^\circ\text{C}$ )	1.7	2.0	2.5	
	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 50A, T_j = 125^\circ\text{C}$ )		2.2		
$I_{CES}$	Collector Cut-off Current ( $V_{CE} = 600V, V_{GE} = 0V, T_j = 25^\circ\text{C}$ ) <sup>2</sup>			50	$\mu\text{A}$
	Collector Cut-off Current ( $V_{CE} = 600V, V_{GE} = 0V, T_j = 125^\circ\text{C}$ ) <sup>2</sup>			1250	
$I_{GES}$	Gate-Emitter Leakage Current ( $V_{GE} = \pm 20V$ )			120	nA

 CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

## DYNAMIC CHARACTERISTICS

## APT50GT60BRDL(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT	
$C_{ies}$	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		2500		pF	
$C_{oes}$	Output Capacitance			250			
$C_{res}$	Reverse Transfer Capacitance			155			
$V_{GEP}$	Gate-to-Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 300V$ $I_C = 50A$		7.5		V	
$Q_g$	Total Gate Charge <sup>3</sup>			240		nC	
$Q_{ge}$	Gate-Emitter Charge			20			
$Q_{gc}$	Gate-Collector ("Miller") Charge			110			
SSOA	Switching Safe Operating Area	$T_J = 150^\circ\text{C}, R_G = 5\Omega, V_{GE} = 15V, L = 100\mu\text{H}, V_{CE} = 600V$	150			A	
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 50A$ $R_G = 5\Omega$ $T_J = +25^\circ\text{C}$		14		ns	
$t_r$	Current Rise Time			32			
$t_{d(off)}$	Turn-off Delay Time			240			
$t_f$	Current Fall Time			36			
$E_{on1}$	Turn-on Switching Energy <sup>4</sup>				995		$\mu\text{J}$
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>5</sup>				1110		
$E_{off}$	Turn-off Switching Energy <sup>6</sup>				1070		
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 50A$ $R_G = 5\Omega$ $T_J = +125^\circ\text{C}$		14		ns	
$t_r$	Current Rise Time			32			
$t_{d(off)}$	Turn-off Delay Time			270			
$t_f$	Current Fall Time			95			
$E_{on1}$	Turn-on Switching Energy <sup>4</sup>				1035		$\mu\text{J}$
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>5</sup>				1655		
$E_{off}$	Turn-off Switching Energy <sup>6</sup>				1505		

## THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.28	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction to Case (DIODE)			.61	
$W_T$	Package Weight		5.9		gm

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② For Combi devices,  $I_{ces}$  includes both IGBT and FRED leakages
- ③ See MIL-STD-750 Method 3471.
- ④  $E_{on1}$  is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.
- ⑤  $E_{on2}$  is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)
- ⑥  $E_{off}$  is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)
- ⑦ Continuous current limited by package lead temperature.

Microsemi Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT50GT60BRDL(G)

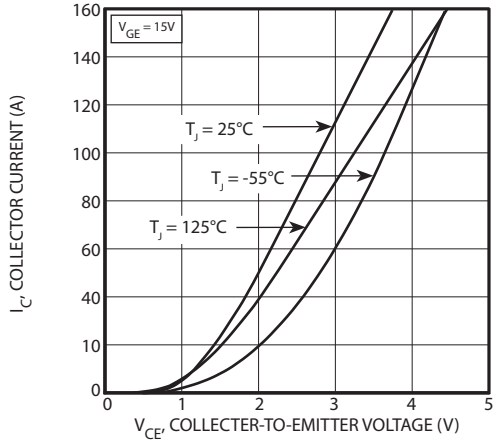


FIGURE 1, Output Characteristics ( $T_J = 25^\circ\text{C}$ )

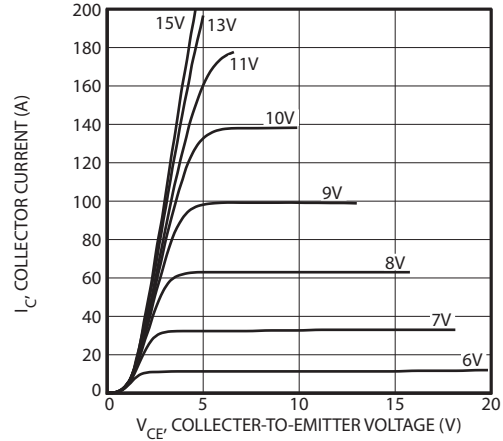


FIGURE 2, Output Characteristics ( $T_J = 125^\circ\text{C}$ )

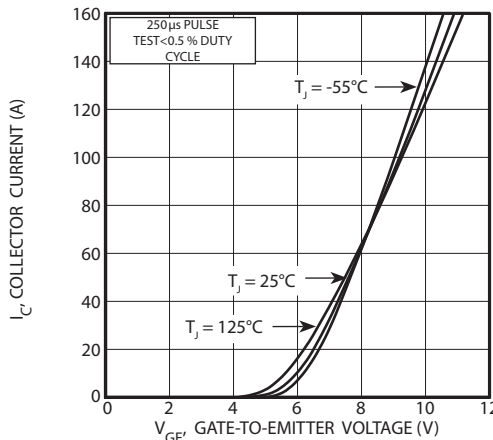


FIGURE 3, Transfer Characteristics

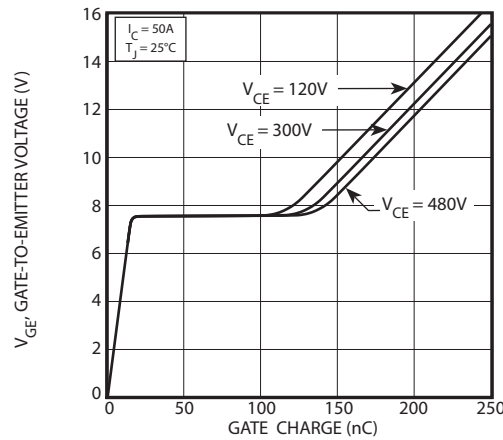


FIGURE 4, Gate Charge

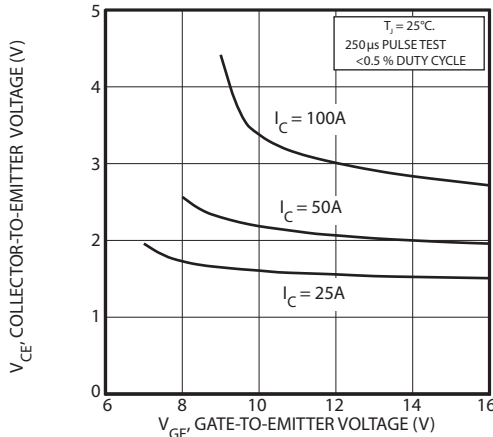


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

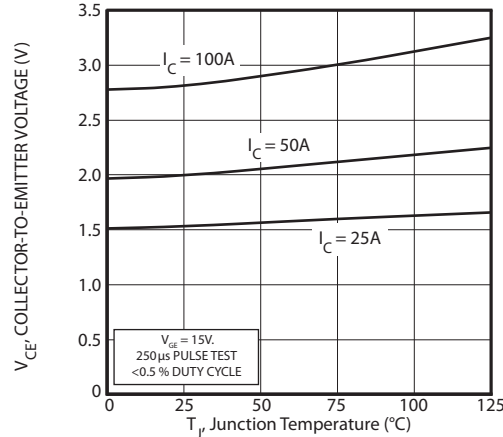


FIGURE 6, On State Voltage vs Junction Temperature

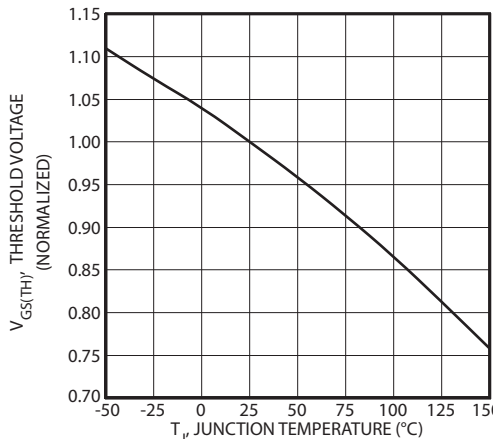


FIGURE 7, Threshold Voltage vs. Junction Temperature

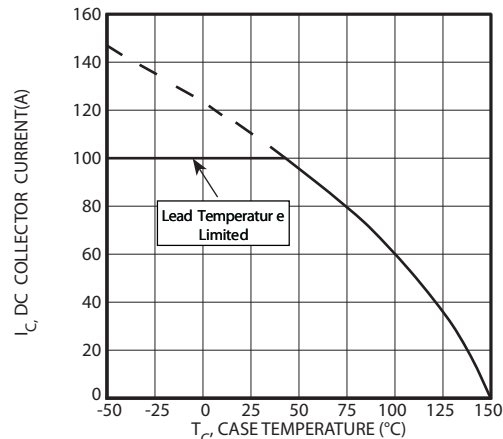


FIGURE 8, DC Collector Current vs Case Temperature

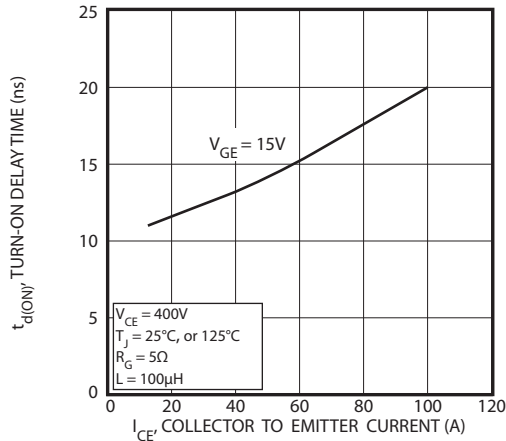


FIGURE 9, Turn-On Delay Time vs Collector Current

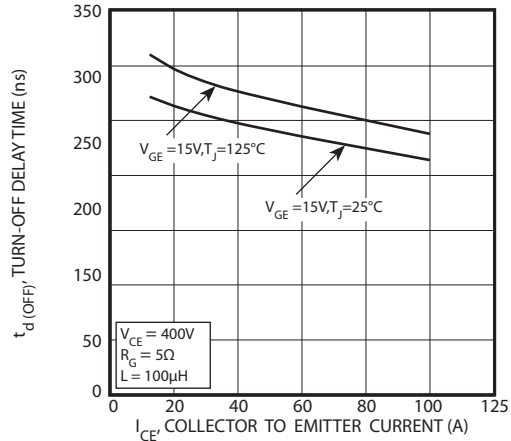


FIGURE 10, Turn-Off Delay Time vs Collector Current

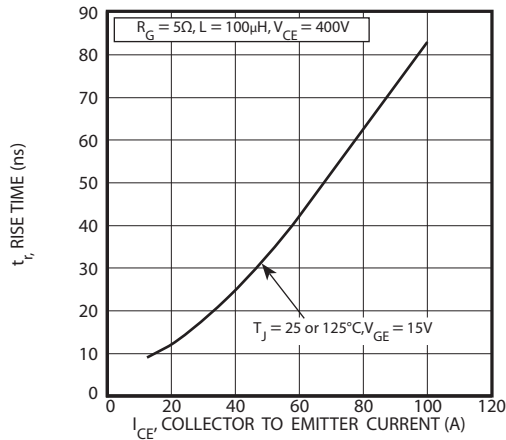


FIGURE 11, Current Rise Time vs Collector Current

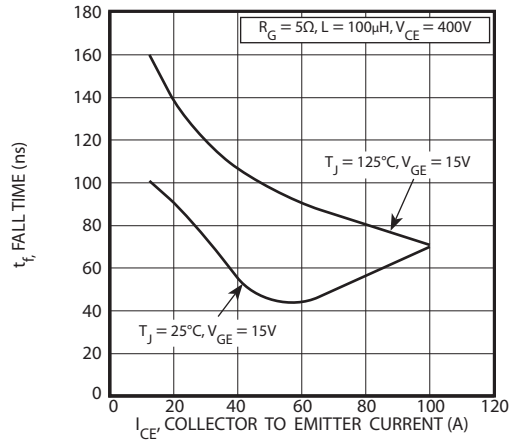


FIGURE 12, Current Fall Time vs Collector Current

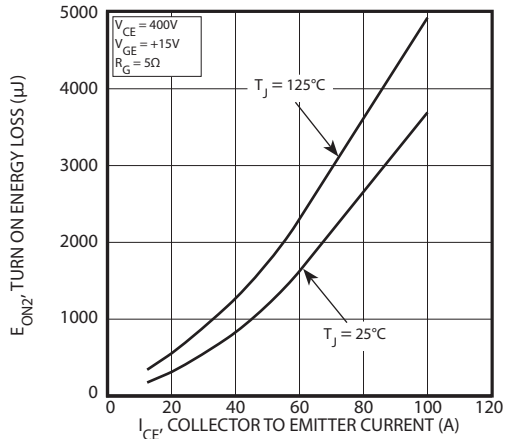


FIGURE 13, Turn-On Energy Loss vs Collector Current

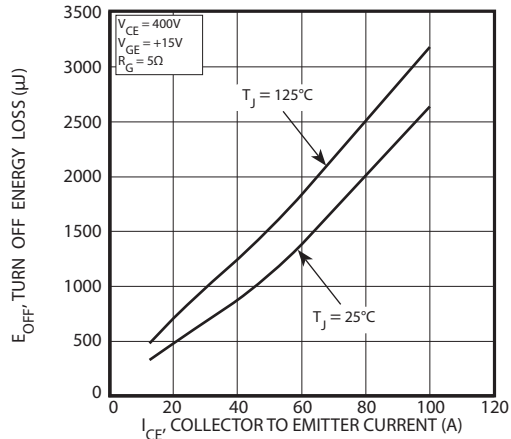


FIGURE 14, Turn Off Energy Loss vs Collector Current

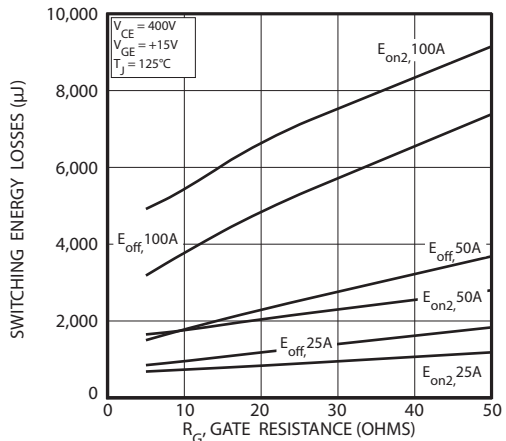


FIGURE 15, Switching Energy Losses vs. Gate Resistance

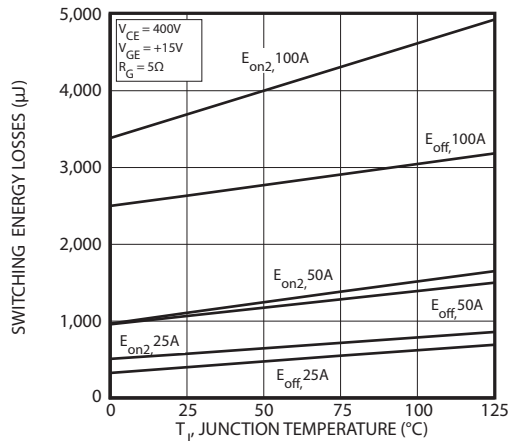


FIGURE 16, Switching Energy Losses vs Junction Temperature

TYPICAL PERFORMANCE CURVES

APT50GT60BRDL(G)

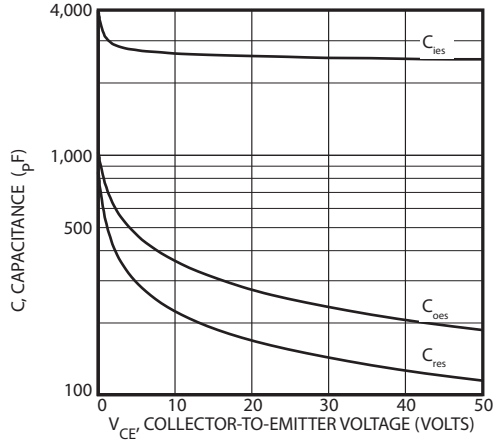


Figure 17, Capacitance vs Collector-To-Emitter Voltage

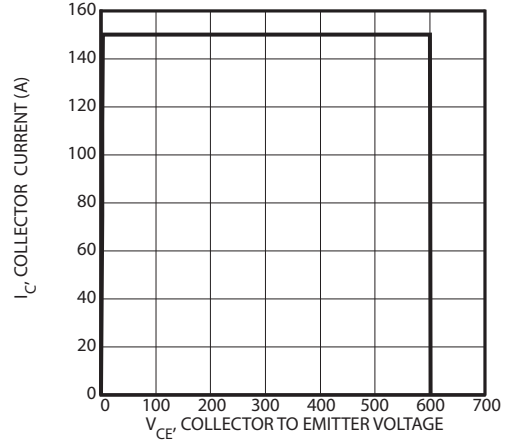


Figure 18, Minimum Switching Safe Operating Area

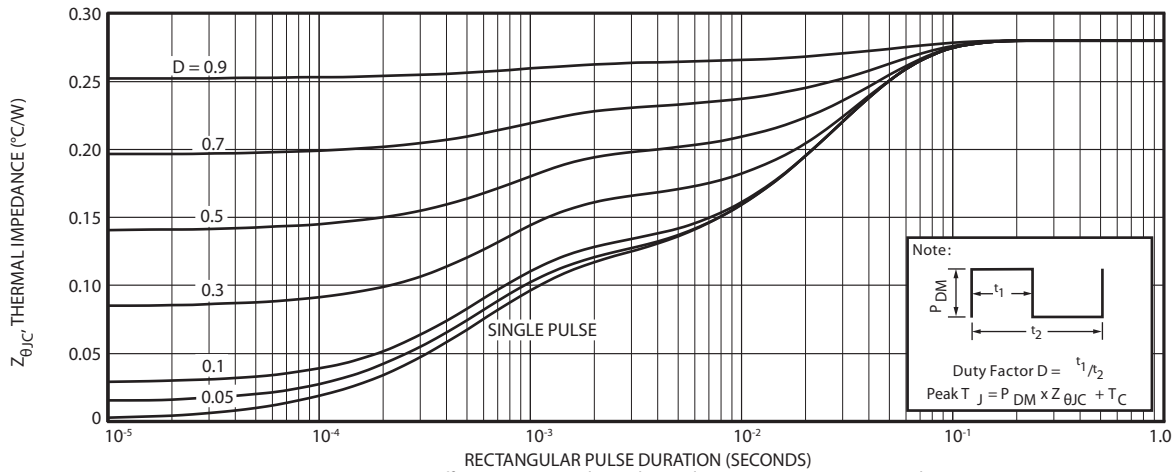


Figure 19a, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

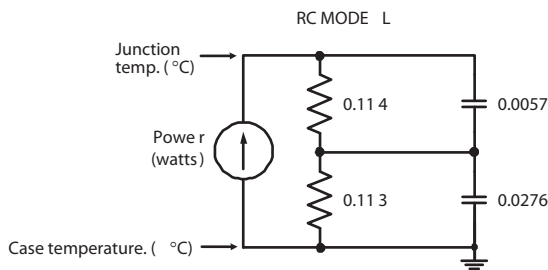


FIGURE 19b, TRANSIENT THERMAL IMPEDANCE MODEL

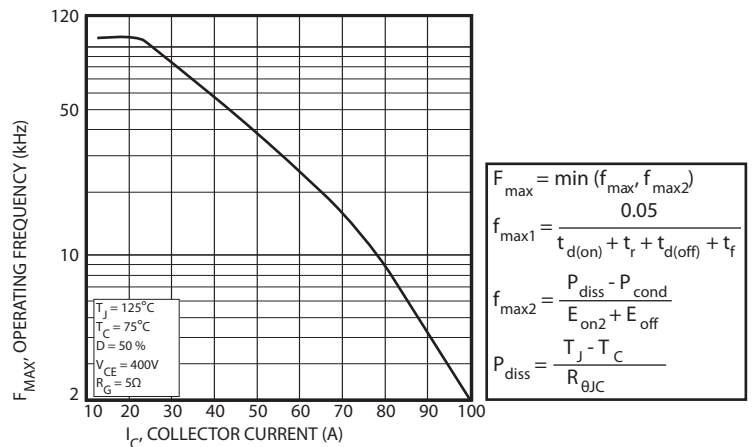


Figure 20, Operating Frequency vs Collector Current

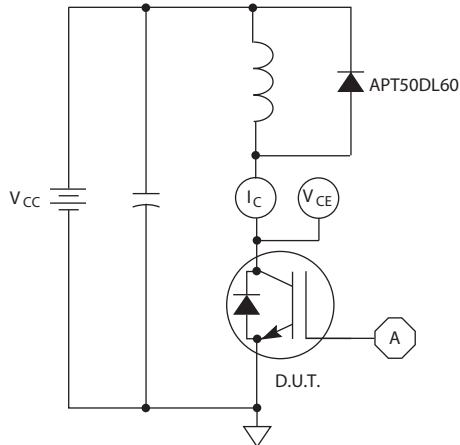


Figure 21, Inductive Switching Test Circuit

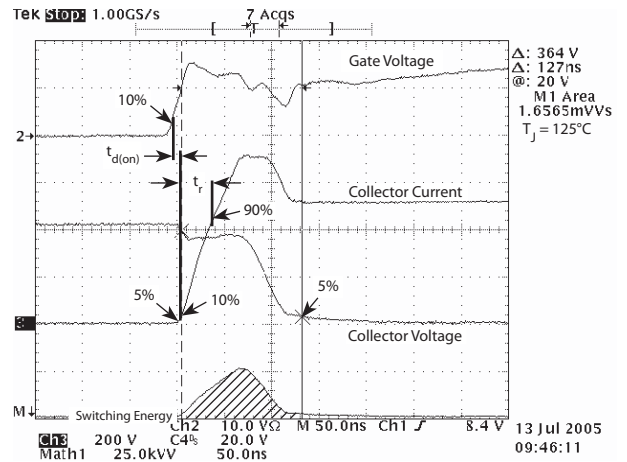


Figure 22, Turn-on Switching Waveforms and Definitions

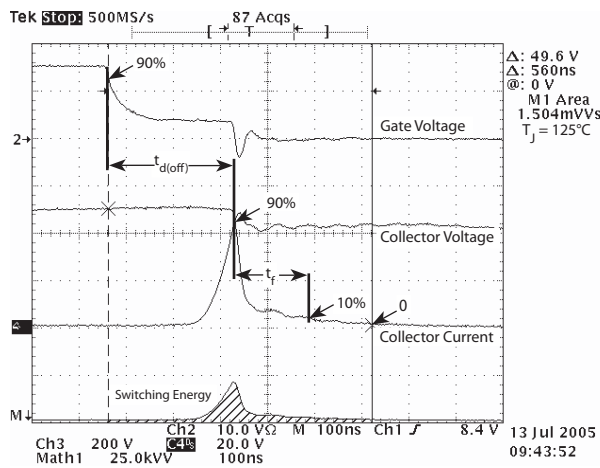


Figure 23, Turn-off Switching Waveforms and Definitions

# ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT50GT60BRDL(G)			UNIT
$I_{F(AV)}$	Maximum Average Forward Current ( $T_C = 100^\circ\text{C}$ , Duty Cycle = 0.5)		50		Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)		150		
$I_{FSM}$	Non-Repetitive Forward Surge Current ( $T_J = 45^\circ\text{C}$ , 8.3ms)		320		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT	
$V_F$	Forward Voltage	$I_F = 50\text{A}$		1.25	1.6	Volts
		$I_F = 100\text{A}$		2.0		
		$I_F = 50\text{A}, T_J = 125^\circ\text{C}$		1.25		

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$t_{rr}$	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	52		ns
$t_{rr}$	Reverse Recovery Time	$I_F = 50\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 25^\circ\text{C}$	-	399		
$Q_{rr}$	Reverse Recovery Charge		-	1498		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	9	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 50\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	649		ns
$Q_{rr}$	Reverse Recovery Charge		-	3734		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	13	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 50\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	284		ns
$Q_{rr}$	Reverse Recovery Charge		-	5134		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	34		Amps

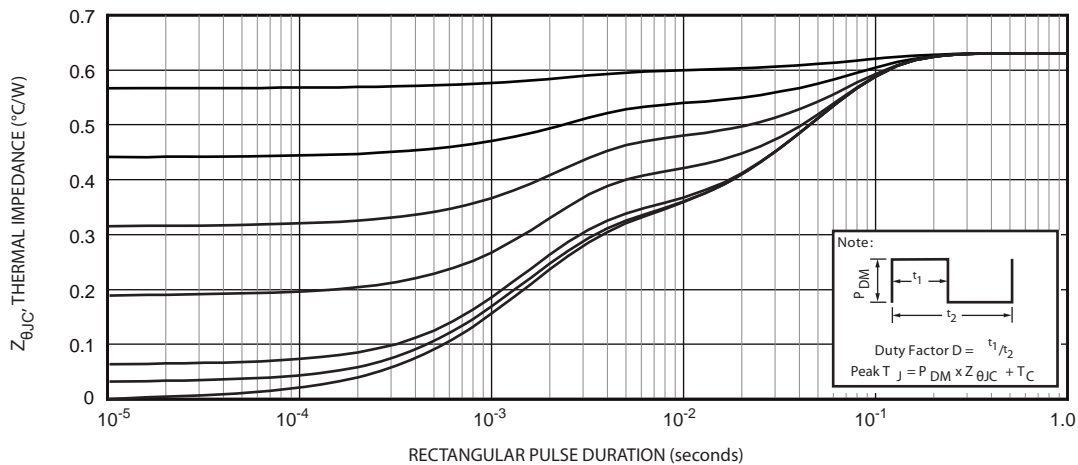


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

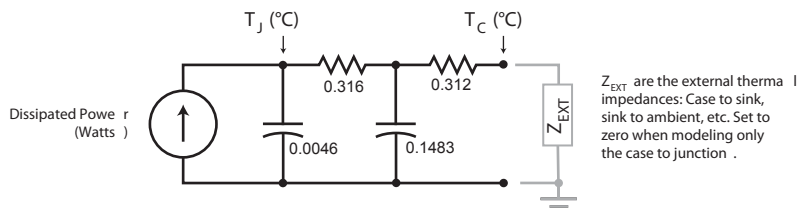


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

TYPICAL PERFORMANCE CURVES

APT50GT60BRDL(G)

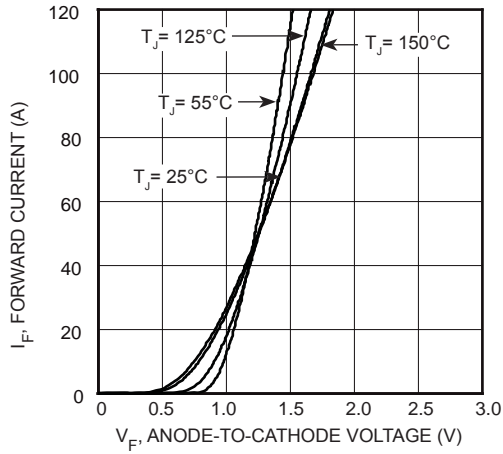


FIGURE 2, Forward Current vs. Forward Voltage

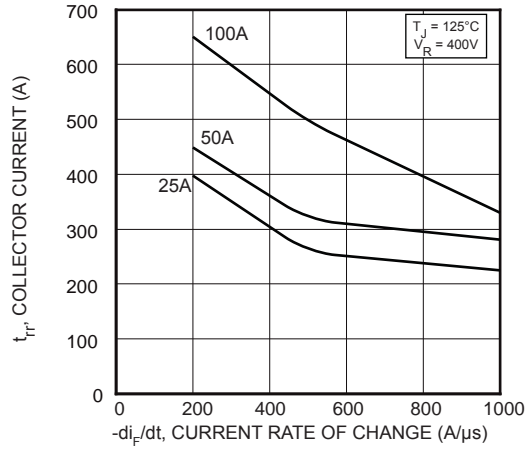


FIGURE 3, Reverse Recovery Time vs. Current Rate of Change

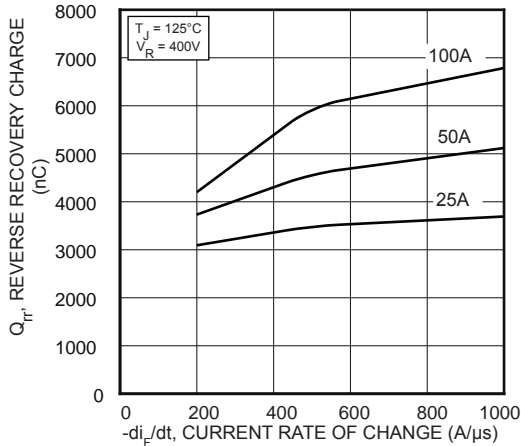


FIGURE 4, Reverse Recovery Charge vs. Current Rate of Change

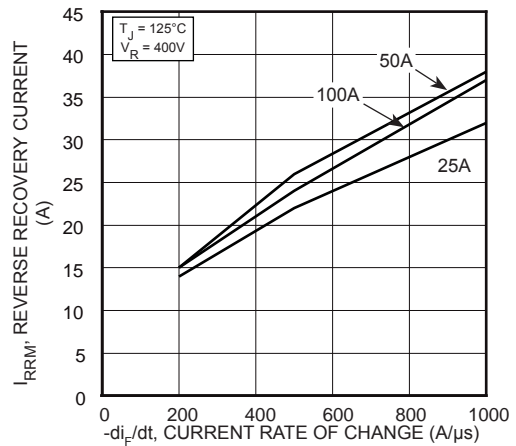


FIGURE 5, Reverse Recovery Current vs. Current Rate of Change

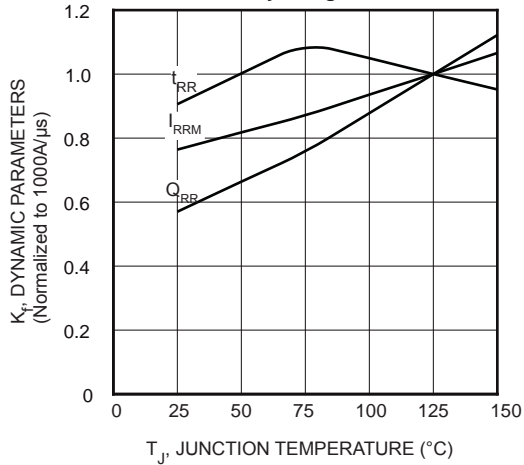


FIGURE 6, Dynamic Parameters vs Junction Temperature

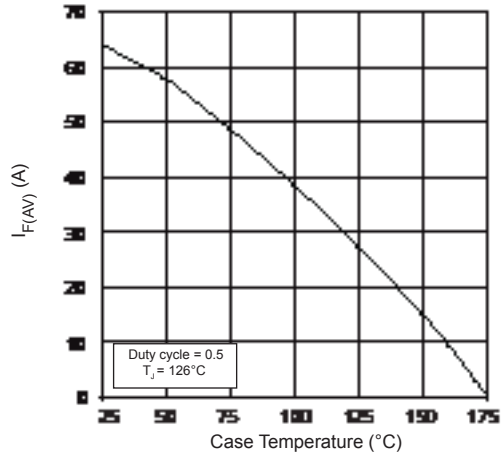


FIGURE 7, Maximum Average Forward Current vs. Case Temperature

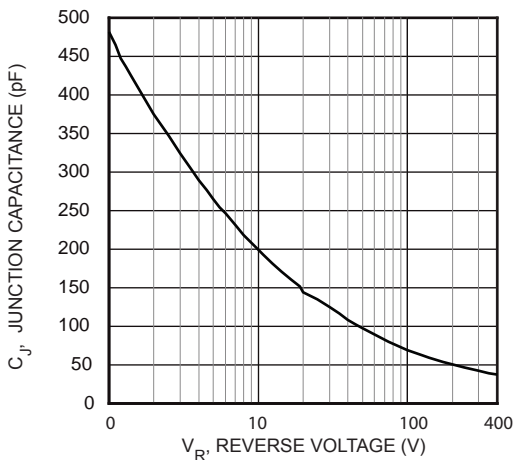


FIGURE 8, Junction Capacitance vs. Reverse Voltage



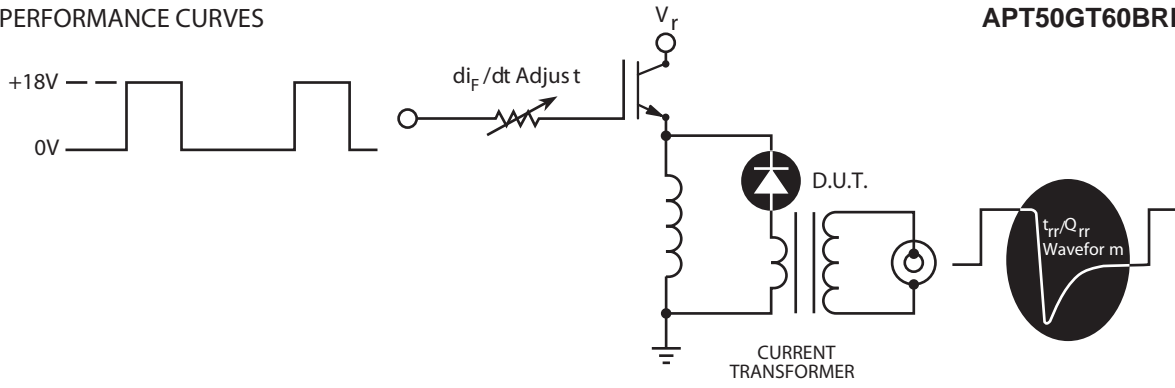


Figure 9. Diode Test Circuit

- 1  $I_F$  - Forward Conduction Current
- 2  $di_F/dt$  - Rate of Diode Current Change Through Zero Crossing.
- 3  $I_{RRM}$  - Maximum Reverse Recovery Current
- 4  $t_{rr}$  - Reverse Recovery Time, measured from zero crossing where the diode current goes from positive to negative, to the point at which the straight line through  $I_{RRM}$  and  $0.25 I_{RRM}$  passes through zero.
- 5  $Q_{rr}$  - Area Under the Curve Defined by  $I_{RRM}$  and  $t_{rr}$ .
- 6  $di_M/dt$  - Maximum Rate of Current Increase During the Trailing Portion of  $t_{rr}$ .

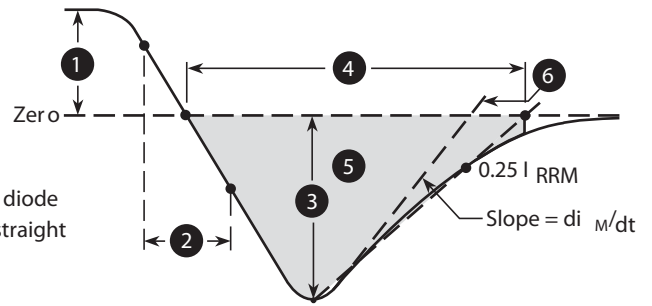
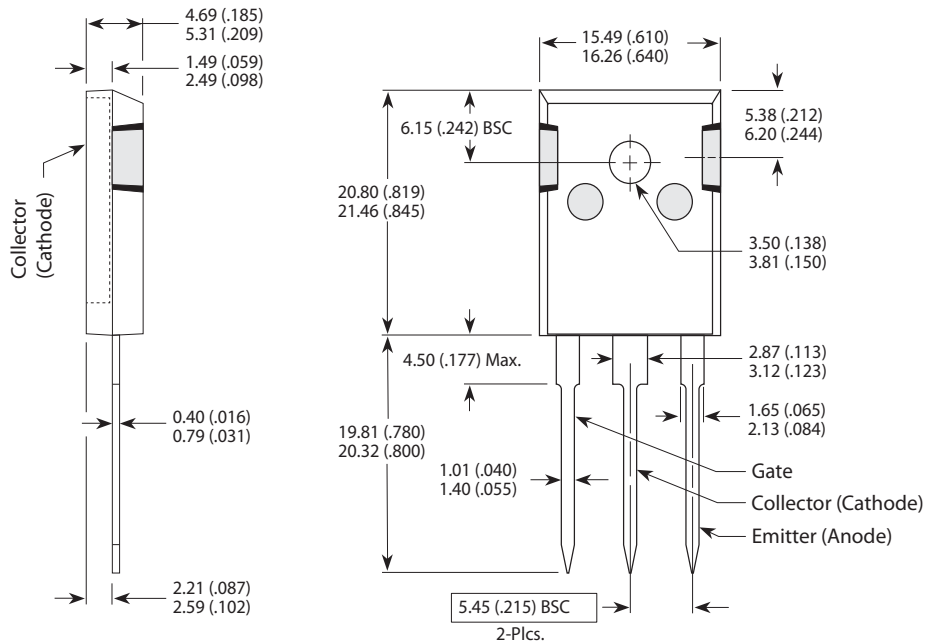


Figure 10, Diode Reverse Recovery Waveform and Definition

TO-247 (B) Package Outline



Dimensions in Millimeters and (Inches)